

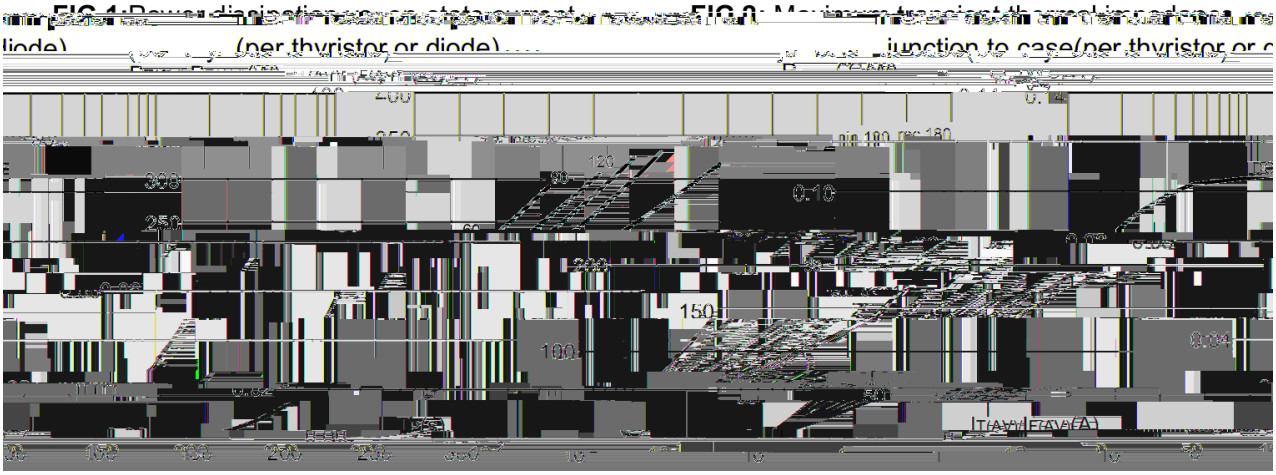
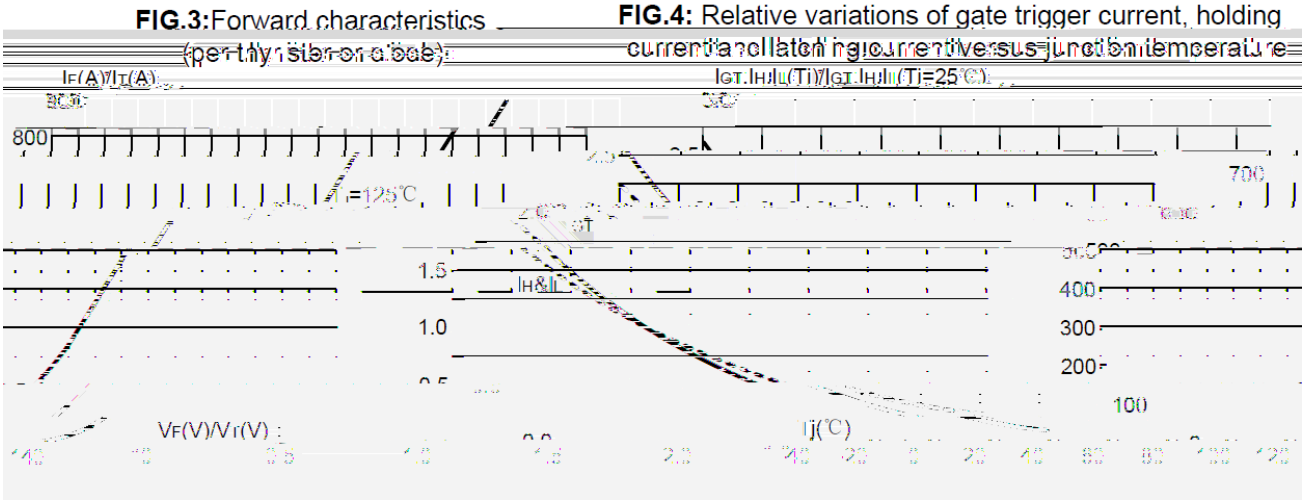
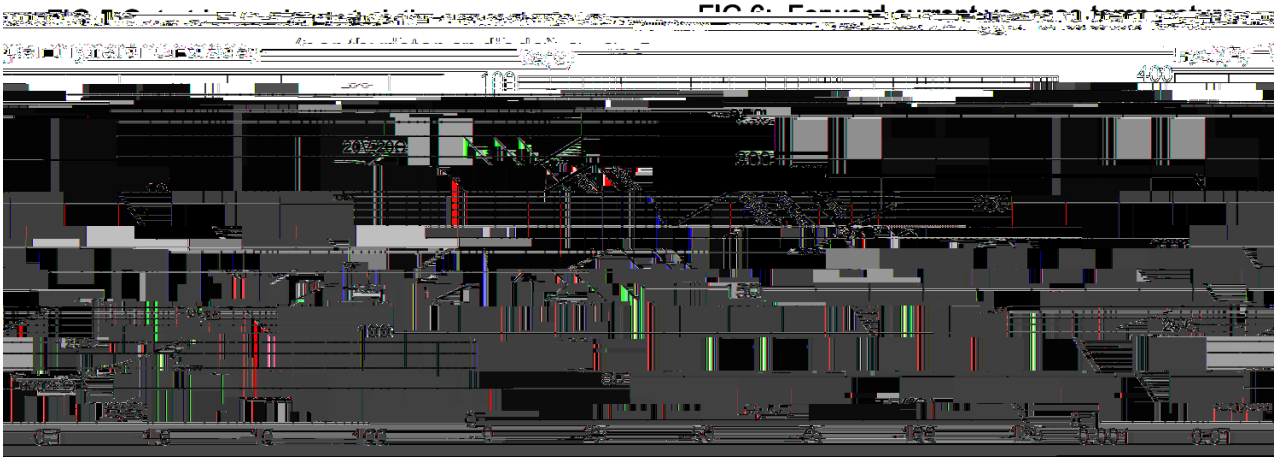
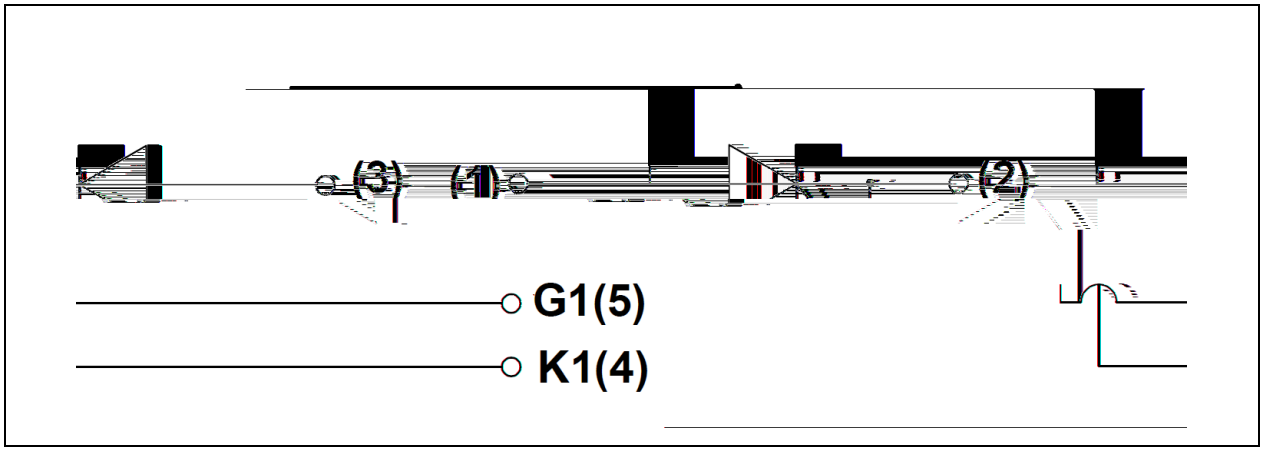


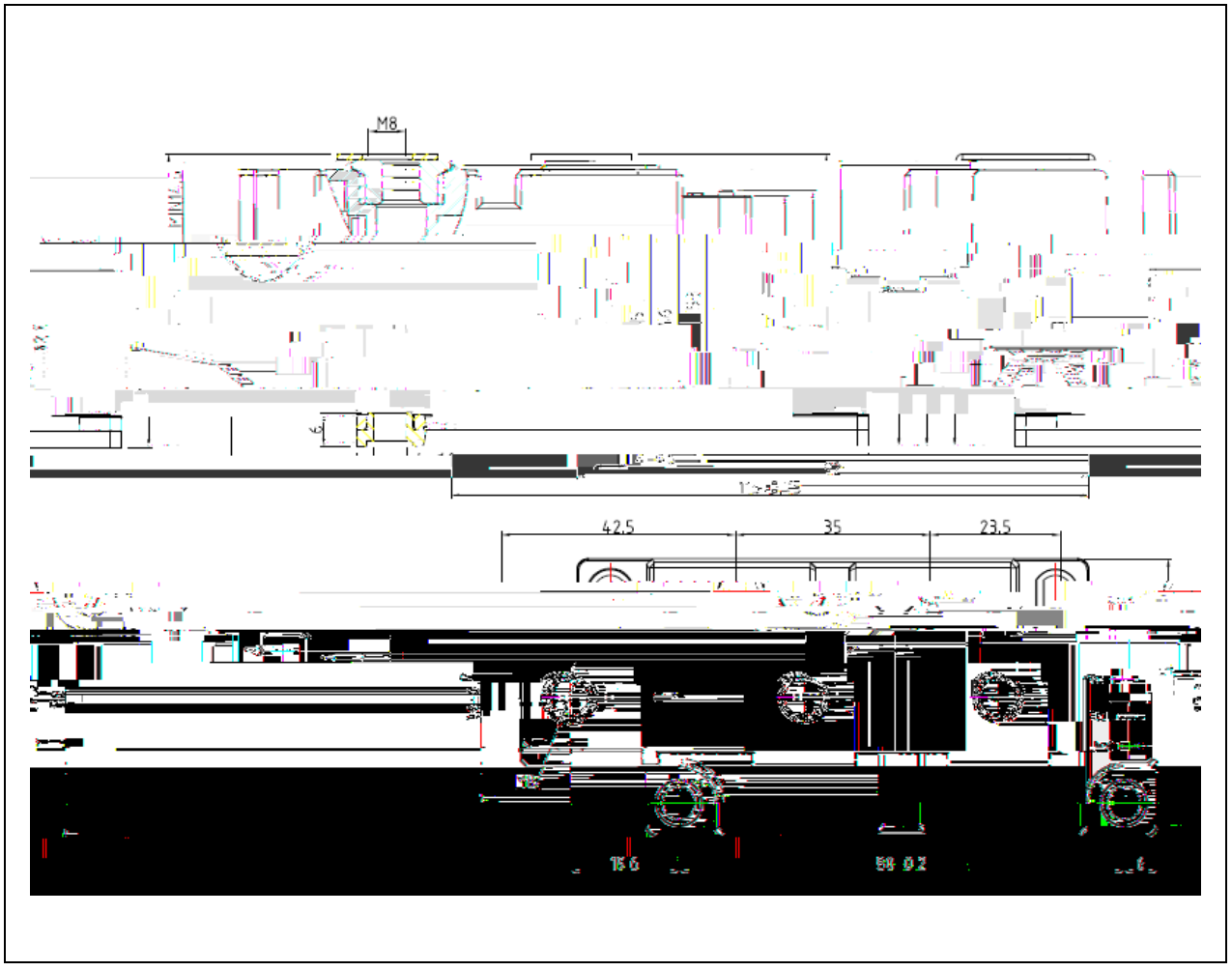
FIG.3: Forward characteristics (per thyristor or diode)

FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature






(3)
(1)
(2)
G1(5)
K1(4)


M8
42.5
35
23.5